First Named Inventor	Leonard Forbes		
secial No.	10/808,059		
Filing Date	March 24, 2004		
oup Art Unit	2814		
Examiner Name	Marcos D. Pizarro Crespo		
Confirmation No.	4221		
Attorney Docket No.	400.285US01		

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Title: NROM MEMORY DEVICE WITH HIGH-PERMITTIVITY GATE DIELECTRIC FORMED BY THE LOW TEMPERATURE OXIDIZATION OF METALS

Mail Stop: AMENDMENT Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

In compliance with 37 C.F.R. §§ 1.56 and 1.97, et seq., the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified Application. Pursuant to 37 C.F.R. 1.98 (a)(2)(i), as this application was filed after June 30, 2003, Applicant has not included copies of U.S. Patents or U.S. Patent Application Publications. Applicant respectfully requests that this Supplemental Information Disclosure Statement be entered and the references listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to MPEP §609, Applicant further requests that the Examiner initial next to each reference on the Form 1449 to indicate that the listed references have been considered. Applicant further requests that a copy of the initialed Form 1449 be returned with the next official communication.

As an Office Action has issued in this application, Applicant encloses a check in the amount of \$180.00. The Commissioner for Patents is hereby authorized to charge any additional fees to Deposit Account No. 501373.

If the Examiner has any questions or concerns regarding this application, please contact the undersigned at (612) 312-2204.

Respectfully submitted,

Thomas W. Leffert Reg. No. 40,697

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Title: NROM MEMORY DEVICE WITH HIGH-PERMITTIVITY GATE DIELECTRIC FORMED BY THE LOW TEMPERATURE OXIDIZATION OF METALS

Sheet 1 of 1

U.S. Patent References					
Examiner Initials	Document No.	Issue/Publication Date	Name	Filing Date	
	2005-0173755	08/11/2005	Forbes	02/10/2004	
	2005-0275011	12/15/2005	Forbes	08/24/2005	
··	2006-0019453	01/26/2006	Forbes	08/22/2005	

Foreign Patent References						
Examiner	Foreign Pate	ent	1	Vame	Publication	Translation
Initials	Country	No.			Date	

Other References				
Examiner Initials	Author, Title, Date, Pages, etc.			

Examiner		Date		
Signature		Considered		
*Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not				